

1. Scope :

This specification applies to NP silicon UV-enhanced photodiode chips,
Device No. PD-26236U-B.

2. Structure :

- 2-1. Planar type : NP diode.
- 2-2. Electrodes :
Top side (Cathode) : Aluminum alloy .
Back side (Anode) : Gold .

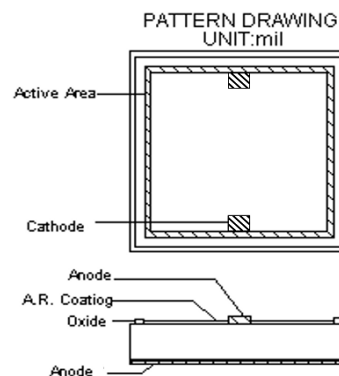
3. Size :

- 3-1. Chip size : 236 mils x 236 mils (6.000 mm x 6.000 mm).
- 3-2. Chip thickness : 15.7 mils ± 1.5 mils (0.400 ± 0.038 mm).
- 3-3. Active area : 199.84 mils x 199.84 mils (5.706 mm x 5.706 mm).
- 3-4. Bonding pad (Cathode) : 6.3 mils x 8.15 mils (0.160mm x 0.207mm).
- 3-5. Pattern drawing : Refer to the attached drawing.

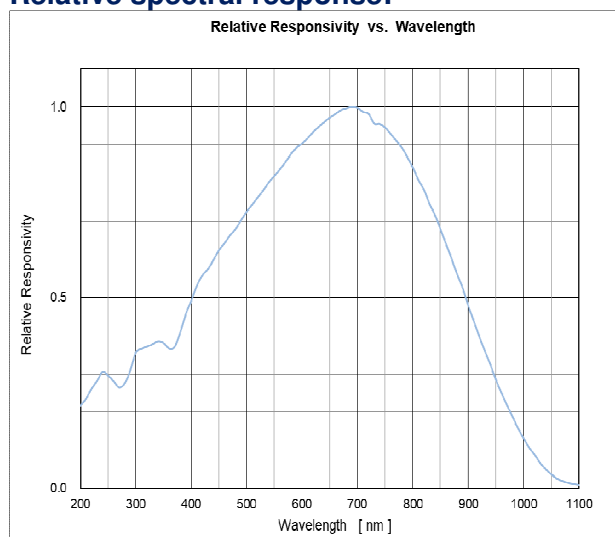
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
**Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			30	nA
**Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	33			V
Sensitivity Wavelength Range	λ	-	300		1100	nm
Peak sensitivity wavelength	λ_p	-		700		nm

**Based on 100% probing.



5. Relative spectral response:



*Bare chip measured, for reference only.